TOSHIBA CMOS Linear Integrated Circuit Silicon Monolithic

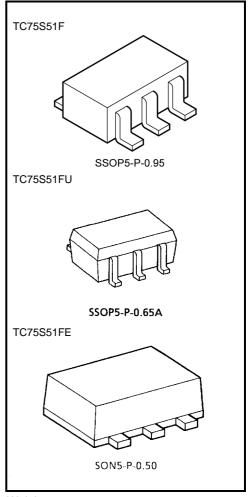
# TC75S51F,TC75S51FU,TC75S51FE

### Single Operational Amplifier

The TC75S51F/TC75S51FU/TC75S51FE is a CMOS single-operation amplifier which incorporates a phase compensation circuit. It is designed for use with a low-voltage, low-current power supply; this differentiates this device from conventional general-purpose bipolar op-amps.

#### **Features**

- Low-voltage operation :  $V_{DD} = \pm 0.75 \sim \pm 3.5 \text{ V} \text{ or } 1.5 \sim 7 \text{ V}$
- Low-current power supply : IDD (VDD = 3 V) = 60  $\mu A$  (typ.)
- Built-in phase-compensated op-amp, obviating the need for any external device
- Ultra-compact package



Weight

SSOP5-P-0.95 : 0.014 g (typ.) SSOP5-P-0.65A : 0.006 g (typ.) SON5-P-0.50 : 0.003 g (typ.)

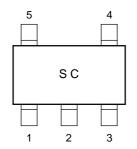
## Maximum Ratings (Ta = 25°C)

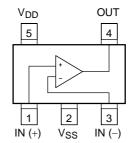
Characteristics		Symbol	Rating	Unit
Supply voltage		V <sub>DD</sub> , V <sub>SS</sub>	7	V
Differential input voltage		DV <sub>IN</sub>	±7	V
Input voltage		V <sub>IN</sub>	$V_{DD} \sim V_{SS}$	V
Power dissipation	TC75S51F/FU	P <sub>D</sub>	200	mW
	TC75S51FE	FD	100	IIIVV
Operating temperature		T <sub>opr</sub>	-40~85	°C
Storage temperature		T <sub>stg</sub>	-55~125	°C

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# Marking (top view)

# Pin Connection (top view)





## **Electrical Characteristics**

# DC Characteristics (V<sub>DD</sub> = 3.0 V, V<sub>SS</sub> = GND, Ta = 25°C)

Characteristics	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Input offset voltage	$V_{IO}$	1	$R_S = 1 \text{ k}\Omega, R_F = 100 \text{ k}\Omega$	_	2	10	mV
Input offset current	I <sub>IO</sub>	_	_	_	1	_	рА
Input bias current	lį	_	_	_	1	_	рА
Common mode input voltage	CMV <sub>IN</sub>	2	$R_S = 1 \text{ k}\Omega, R_F = 100 \text{ k}\Omega$	0	_	2.5	V
Voltage gain (open loop)	G <sub>V</sub>	_	_	60	70	_	dB
Maximum output voltage	V <sub>OH</sub>	3	$R_L \ge 100 \text{ k}\Omega$	2.9	_	_	V
	V <sub>OL</sub>	4	$R_L \ge 100 \text{ k}\Omega$	_	_	0.1	v
Common mode input signal rejection ratio	CMRR	2	V <sub>IN</sub> = 0.0~2.5 V	55	65	_	dB
Supply voltage rejection ratio	SVRR	1	V <sub>DD</sub> = 1.5~7.0 V	60	70	_	dB
Supply current	I <sub>DD</sub>	5	_	_	60	200	μА

# DC Characteristics ( $V_{DD} = 1.5 \text{ V}, V_{SS} = \text{GND}, \text{Ta} = 25^{\circ}\text{C}$ )

Characteristics	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Input offset voltage	V <sub>IO</sub>	1	$R_S = 10 \text{ k}\Omega, R_F = 100 \text{ k}\Omega$	_	2	10	mV
Input offset current	I <sub>IO</sub>	_	_	_	1	_	pА
Input bias current	lį	_	_		1	_	pА
Common mode input voltage	CMV <sub>IN</sub>	2	$R_S = 10 \text{ k}\Omega, R_F = 100 \text{ k}\Omega$	0	_	1.0	V
Voltage gain (open loop)	G <sub>V</sub>	_	_	60	70	_	dB
Maximum output voltage	V <sub>OH</sub>	3	$R_L \ge 100 \text{ k}\Omega$	1.4	_	_	V
	V <sub>OL</sub>	4	$R_L \ge 100 \text{ k}\Omega$	_	_	0.1	V
Supply current	I <sub>DD</sub>	5	_	_	50	150	μΑ

Note: For this device, please use a source current of no more than 70  $\mu$ A.

# AC Characteristics (V<sub>DD</sub> = 3.0 V, V<sub>SS</sub> = GND, Ta = 25°C)

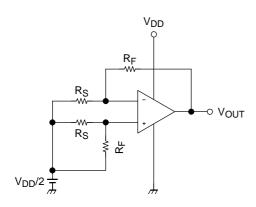
Characteristics	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Slew rate	SR	_	$A_V = 0 dB$	_	0.5	_	V/μs
Unity gain cross frequency	f <sub>T</sub>	_	$A_V = 40 \text{ dB}$	_	0.6	_	MHz

# AC Characteristics (V<sub>DD</sub> = 1.5 V, V<sub>SS</sub> = GND, Ta = 25°C)

Characteristics	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Slew rate	SR	_	$A_V = 0 dB$	_	0.3	_	V/μs
Unity gain cross frequency	f <sub>T</sub>	_	$A_V = 40 \text{ dB}$	_	0.5	_	MHz

#### **Test Circuit**

# 1. SVRR, VIO



#### SVRR

For each of the two  $V_{\mbox{\scriptsize DD}}$  values, measure the  $V_{\mbox{\scriptsize OUT}}$  value, as indicated below, and calculate the value of SVRR using the equation shown.

When 
$$V_{DD}$$
 = 1.5 V,  $V_{DD}$  =  $V_{DD}$ 1 and  $V_{OUT}$  =  $V_{OUT}$ 1 When  $V_{DD}$  = 7.0 V,  $V_{DD}$  =  $V_{DD}$ 2 and  $V_{OUT}$  =  $V_{OUT}$ 2

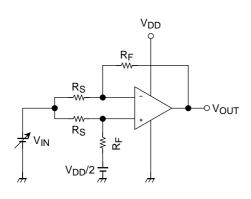
$$SVRR = 20 \log \left( \frac{\left| \frac{V_{OUT}1 - V_{OUT}2}{V_{DD}1 - V_{DD}2} \right| \times \frac{R_S}{R_F + R_S} \right)$$

V<sub>IO</sub>

Measure the value of  $V_{\mbox{\scriptsize OUT}}$  and calculate the value of  $V_{\mbox{\scriptsize IO}}$  using the following equation.

$$V_{IO} = \left(V_{OUT} - \frac{V_{DD}}{2}\right) \times \frac{R_S}{R_F + R_S}$$

#### 2. CMRR, CMV<sub>IN</sub>



#### • CMRR

Measure the  $V_{\mbox{OUT}}$  value, as indicated below, and calculate the value of the CMRR using the equation shown.

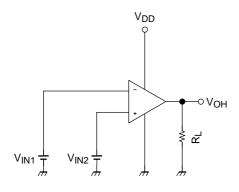
When 
$$V_{IN}$$
 = 0.0 V,  $V_{IN}$  =  $V_{IN}$ 1 and  $V_{OUT}$  =  $V_{OUT}$ 1 When  $V_{IN}$  = 2.5 V,  $V_{IN}$  =  $V_{IN}$ 2 and  $V_{OUT}$  =  $V_{OUT}$ 2

$$CMRR = 20 \log \left( \frac{|V_{OUT}1 - V_{OUT}2|}{|V_{IN}1 - V_{IN}2|} \times \frac{R_S}{R_F + R_S} \right)$$

#### CMV<sub>IN</sub>

Input range within which the CMRR specification guarantees  $V_{\mbox{OUT}}$  value (as varied by the  $V_{\mbox{IN}}$  value).

# 3. V<sub>OH</sub>

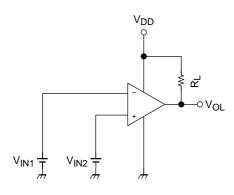


### V<sub>OH</sub>

$$V_{IN1} = \frac{V_{DD}}{2} - 0.05 \text{ V}$$

$$V_{IN2} = \frac{V_{DD}}{2} + 0.05 \text{ V}$$

# 4. V<sub>OL</sub>

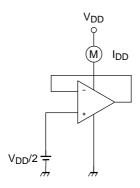


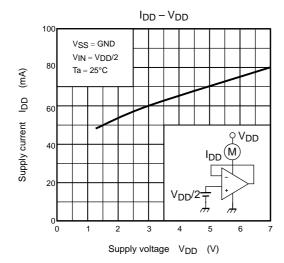
#### V<sub>OL</sub>

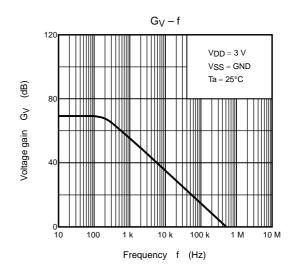
$$V_{IN1} = \frac{V_{DD}}{2} + 0.05 \text{ V}$$

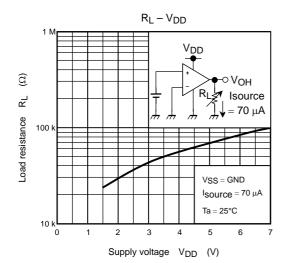
$$V_{IN2} = \frac{V_{DD}}{2} - 0.05 \text{ V}$$

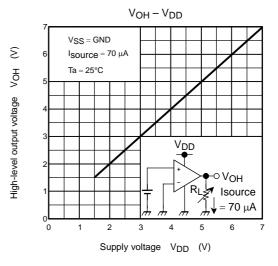
# 5. I<sub>DD</sub>



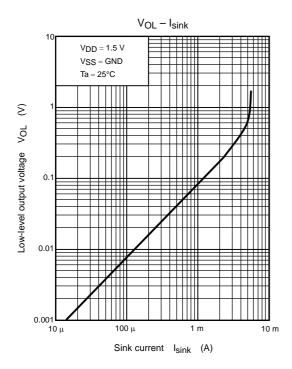


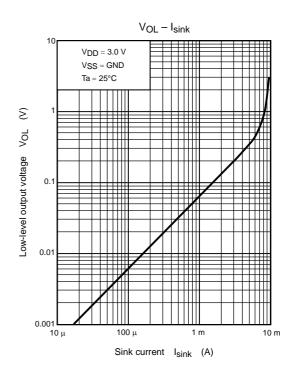


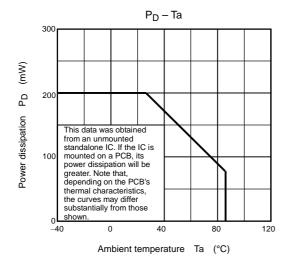




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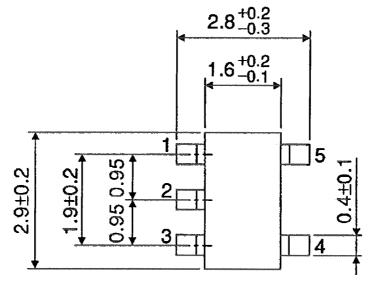


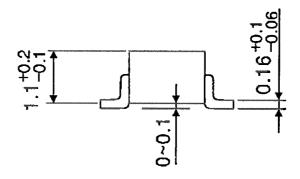
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# **Package Dimensions**

SSOP5-P-0.95 Unit: mm



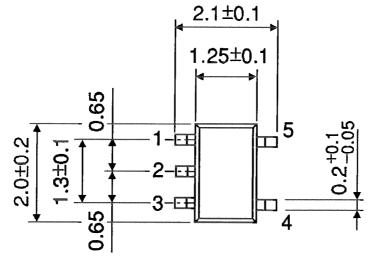


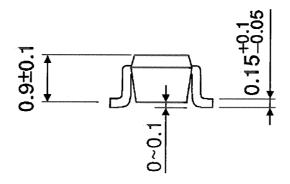
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Weight: 0.014 g (typ.)

# **Package Dimensions**

SSOP5-P-0.65A Unit: mm





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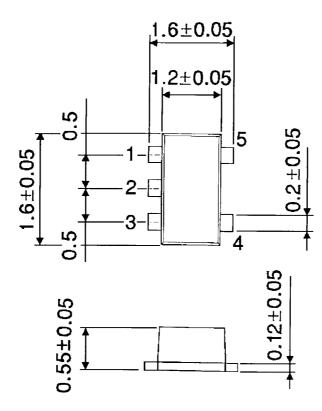
Weight: 0.006 g (typ.)

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# **Package Dimensions**

SON5-P-0.50 Unit: mm



Weight: 0.003 g (typ.)

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